

FEMTOCLOCKS™ CRYSTAL-TO-3.3V LVPECL FREQUENCY SYNTHESIZER

ICS843242

GENERAL DESCRIPTION



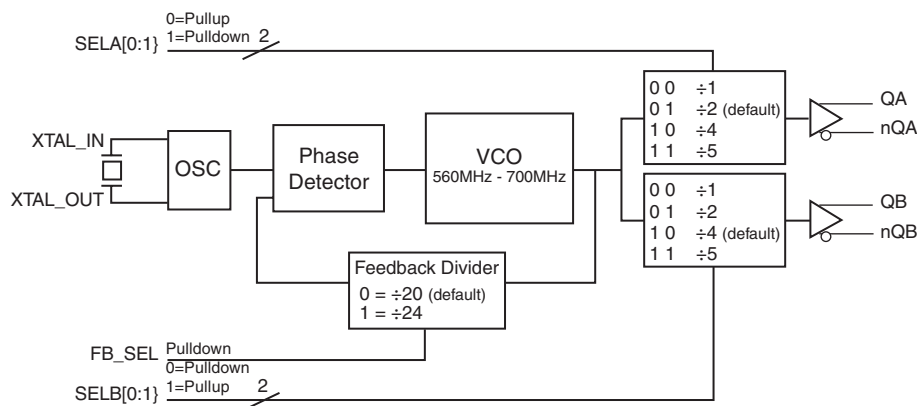
The ICS843242 is a 2 differential output LVPECL Synthesizer designed to generate Ethernet reference clock frequencies and is a member of the HiPerClocks™ family of high performance clock solutions from IDT. Using a 31.25MHz or 26.041666MHz, 18pF parallel resonant crystal, the following frequencies can be generated based on the settings of 4 frequency select pins (SEL[A1:A0], SEL[B1:B0]): 625MHz, 312.5MHz, 156.25MHz, and 125MHz.

The two banks have their own dedicated frequency select pins and can be independently set for the frequencies mentioned above. The ICS843242 IDT's 3rd generation low phase noise VCO technology and can achieve 1ps or lower typical rms phase jitter, easily meeting Ethernet jitter requirements. The ICS843242 is packaged in a small 16-pin TSSOP package.

FEATURES

- Two 3.3V differential LVPECL output pairs
- Using a 31.25MHz or 26.041666 crystal, the two output banks can be independently set for 625MHz, 312.5MHz, 156.25MHz or 125MHz
- Crystal oscillator interface
- VCO range: 560MHz to 700MHz
- RMS phase jitter @ 625MHz (1.875MHz - 20MHz): 0.4ps (typical)
- Full 3.3V supply mode
- 0°C to 70°C ambient operating temperature
- Industrial temperature available upon request
- Available in both standard (RoHS 5) and lead-free (RoHS 6) compliant packages

BLOCK DIAGRAM



PIN ASSIGNMENT

nQB	1	16	XTAL_IN
QB	2	15	XTAL_OUT
Vcco_B	3	14	VEE
SELB1	4	13	SELA1
SELB2	5	12	SELA0
Vcco_A	6	11	Vcc
QA	7	10	VCCA
nQA	8	9	FB_SEL

ICS843242
16-Lead TSSOP
 4.4mm x 5.0mm x 0.92mm
 package body
G Package
 Top View

The Preliminary Information presented herein represents a product in pre-production. The noted characteristics are based on initial product characterization and/or qualification. Integrated Device Technology, Incorporated (IDT) reserves the right to change any circuitry or specifications without notice.

TABLE 1. PIN DESCRIPTIONS

Νόμ βερ	Νομ ε	Τύπε		Δεσχηπτον
1, 2	nQB, QB	Output		Differential clock outputs. LVPECL interface levels.
3	V _{CCO_B}	Power		Output supply pin for QB, nQB outputs.
4	SELB1	Input	Pullup	Division select pin for Bank B. Default = High. LVCMOS/LVTTL interface levels.
5	SELB0	Input	Pulldown	Division select pin for Bank B. Default = Low. LVCMOS/LVTTL interface levels.
6	V _{CCO_A}	Power		Output supply pin for QA, nQA outputs.
7, 8	QA, nQA	Output		Differential clock outputs. LVPECL interface levels.
9	FB_SEL	Input	Pulldown	Feedback divide select. When Low (default), the feedback divider is set for ÷20. When HIGH, the feedback divider is set for ÷24. LVCMOS/LVTTL interface levels.
10	V _{CCA}	Power		Analog supply pin.
11	V _{CC}	Power		Core supply pin.
12	SELA0	Input	Pullup	Division select pin for Bank A. Default = HIGH. LVCMOS/LVTTL interface levels.
13	SELA1	Input	Pulldown	Division select pin for Bank A. Default = Low. LVCMOS/LVTTL interface levels.
14	V _{EE}	Power		Negative supply pin.
15, 16	XTAL_OUT, XTAL_IN	Input		Crystal oscillator interface. XTAL_IN is the input, XTAL_OUT is the output.

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, Pin Characteristics, for typical values.

TABLE 2. PIN CHARACTERISTICS

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			4		pF
R _{PULLDOWN}	Input Pulldown Resistor			51		kΩ
R _{PULLUP}	Input Pullup Resistor			51		kΩ

TABLE 3A. BANK A FREQUENCY TABLE

Inputs				Feedback Divider	Bank A Output Divider	M/N Multiplication Factor	QA/nQA Output Frequency
Crystal Frequency	SELA1	SELA0	FB_SEL				
31.25	0	0	0	20	1	20	625
31.25	0	1	0	20	2	10	312.5
31.25	1	0	0	20	4	5	156.25
31.25	1	1	0	20	5	4	125
26.041666	0	0	1	24	1	24	625
26.041666	0	1	1	24	2	12	312.5
26.041666	1	0	1	24	4	6	156.25
26.041666	1	1	1	24	5	4.8	125

TABLE 3B. BANK B FREQUENCY TABLE

Inputs				Feedback Divider	Bank B Output Divider	M/N Multiplication Factor	QB/nQB Output Frequency
Crystal Frequency	SELA1	SELA0	FB_SEL				
31.25	0	0	0	20	1	20	625
31.25	0	1	0	20	2	10	312.5
31.25	1	0	0	20	4	5	156.25
31.25	1	1	0	20	5	4	125
26.041666	0	0	1	24	1	24	625
26.041666	0	1	1	24	2	12	312.5
26.041666	1	0	1	24	4	6	156.25
26.041666	1	1	1	24	5	4.8	125

TABLE 3C. OUTPUT BANK CONFIGURATION SELECT FUNCTION TABLE

Inputs		Outputs	Inputs		Outputs
SELA1	SELA0	QA	SELB1	SELB0	QB
0	0	÷1	0	0	÷1
0	1	÷2 (default)	0	1	÷2
1	0	÷4	1	0	÷4 (default)
1	1	÷5	1	1	÷5

TABLE 3D. FEEDBACK DIVIDER CONFIGURATION SELECT FUNCTION TABLE

Inputs	
FB_DIV	Feedback Divide
0	÷20 (default)
1	÷24

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V_{CC}	4.6V
Inputs, V_I	-0.5V to $V_{CC} + 0.5V$
Outputs, I_O	
Continuous Current	50mA
Surge Current	100mA
Package Thermal Impedance, θ_{JA}	92.4°C/W (0 mps)
Storage Temperature, T_{STG}	-65°C to 150°C

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

TABLE 4A. POWER SUPPLY DC CHARACTERISTICS, $V_{CC} = V_{CCO_A}, V_{CCO_B} = 3.3V \pm 5\%$, $T_A = 0^\circ\text{C}$ TO 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{CC}	Core Supply Voltage		3.135	3.3	3.465	V
V_{CCA}	Analog Supply Voltage		$V_{CC} - 0.12$	3.3	V_{CC}	V
V_{CCO_A}, V_{CCO_B}	Output Supply Voltage		3.135	3.3	3.465	V
I_{EE}	Power Supply Current			125		mA
I_{CCA}	Analog Supply Current			12		mA

TABLE 4B. LVCMOS / LVTTTL DC CHARACTERISTICS, $V_{CC} = V_{CCO_A} = V_{CCO_B} = 3.3V \pm 5\%$, $T_A = 0^\circ\text{C}$ TO 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage		2		$V_{CC} + 0.3$	V
V_{IL}	Input Low Voltage		-0.3		0.8	V
I_{IH}	Input High Current	FB_SEL, SELA1, SELB0 $V_{CC} = V_{IN} = 3.465V$			150	μA
		SELA0, SELB1 $V_{CC} = V_{IN} = 3.465V$			5	μA
I_{IL}	Input Low Current	FB_SEL, SELA1, SELB0 $V_{CC} = 3.465V, V_{IN} = 0V$	-5			μA
		SELA0, SELB1 $V_{CC} = 3.465V, V_{IN} = 0V$	-150			μA

TABLE 4C. LVPECL DC CHARACTERISTICS, $V_{CC} = V_{CCO_A} = V_{CCO_B} = 3.3V \pm 5\%$, $T_A = 0^\circ\text{C}$ TO 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OH}	Output High Voltage; NOTE 1		$V_{CCO_X} - 1.4$		$V_{CCO_X} - 0.9$	V
V_{OL}	Output Low Voltage; NOTE 1		$V_{CCO_X} - 2.0$		$V_{CCO_X} - 1.7$	V
V_{SWING}	Peak-to-Peak Output Voltage Swing		0.6		1.0	V

NOTE 1: Outputs terminated with 50Ω to $V_{CCO_X} - 2V$.

TABLE 5. CRYSTAL CHARACTERISTICS

Parameter		Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation			Fundamental			
Frequency	FB_SEL = ÷20		28	31.25	35	MHz
	FB_SEL = ÷24		23.33	26.04166	29.167	MHz
Equivalent Series Resistance (ESR)					50	Ω
Shunt Capacitance					7	pF
Drive Level					1	mW

NOTE: Characterized using an 18pF parallel resonant crystal.

TABLE 6. AC CHARACTERISTICS, $V_{CC} = V_{CCO_A}, V_{CCO_B} = 3.3V \pm 5\%$, $T_A = 0^\circ C$ TO $70^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{OUT}	Output Frequency Range	Output Divider = ÷1	490		680	MHz
		Output Divider = ÷2	245		340	MHz
		Output Divider = ÷4	122.5		170	MHz
		Output Divider = ÷5	98		136	MHz
$t_{sk(o)}$	Output Skew; NOTE 1, 3	Outputs @ Same Frequency		20		ps
		Outputs @ Different Frequencies		30		ps
$t_{jit}(\emptyset)$	RMS Phase Jitter (Random); NOTE 2	625MHz (1.875MHz - 20MHz)		0.4		ps
		312.5MHz (1.875MHz - 20MHz)		0.5		ps
		156.25MHz (1.875MHz - 20MHz)		0.5		ps
		125MHz (1.875MHz - 20MHz)		0.6		ps
t_R / t_F	Output Rise/Fall Time	20% to 80%		300		ps
odc	Output Duty Cycle	SELx[1:0] = 00		50		%
		SELx[1:0] ≠ 00		50		%

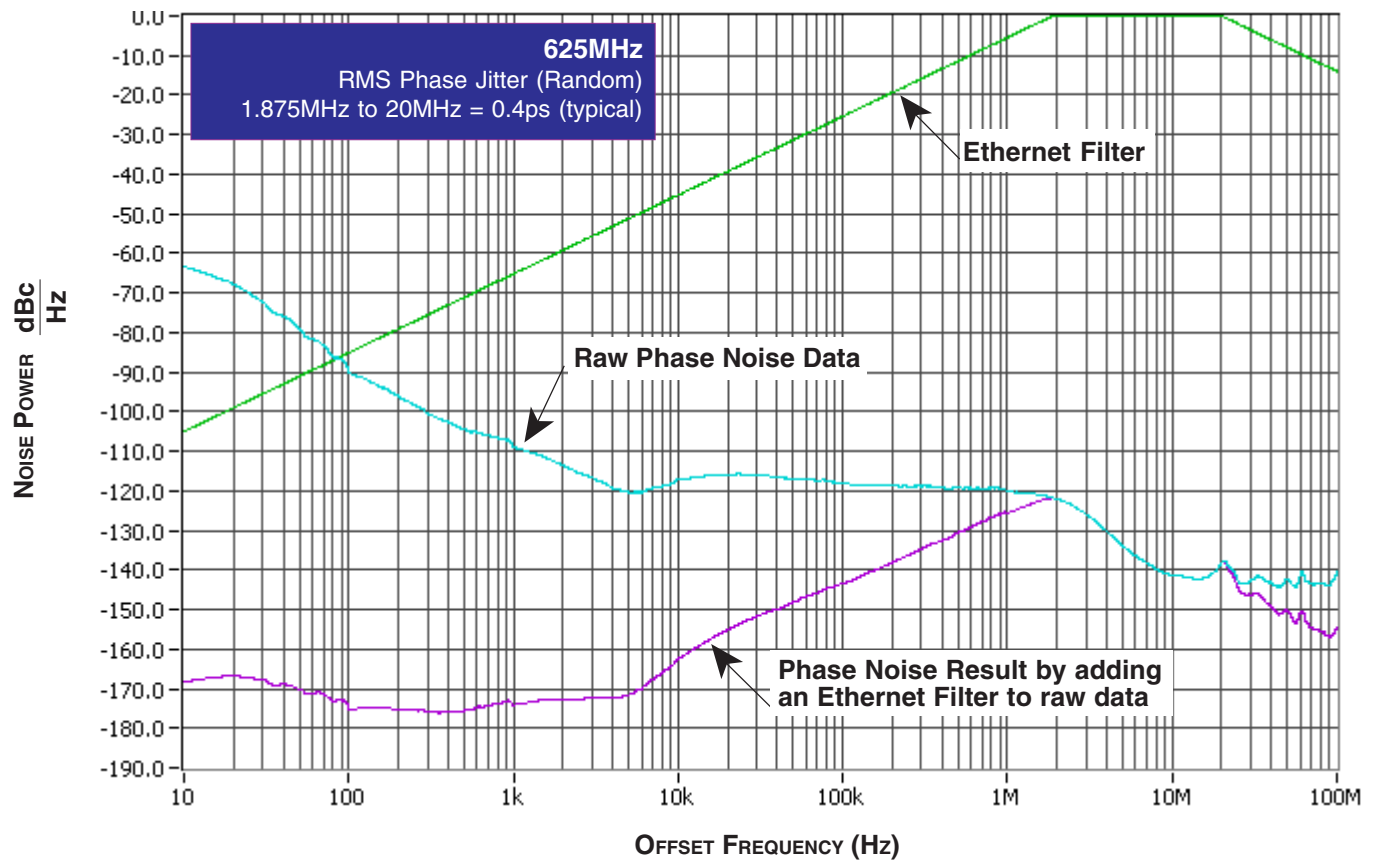
NOTE 1: Defined as skew between outputs at the same supply voltages and with equal load conditions.

Measured at the output differential cross points.

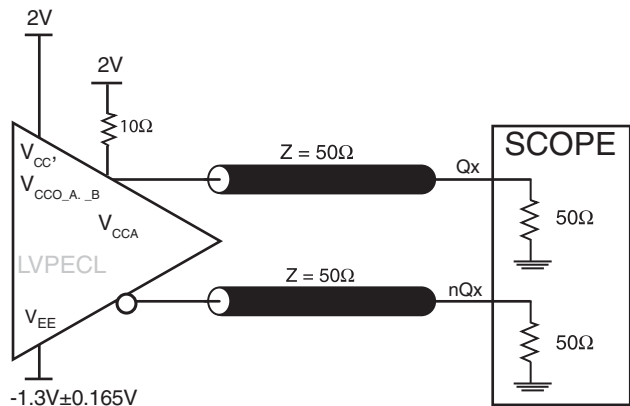
NOTE 2: Please refer to the Phase Noise Plots.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

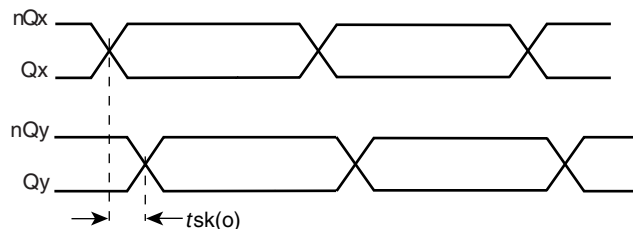
TYPICAL PHASE NOISE AT 625MHz



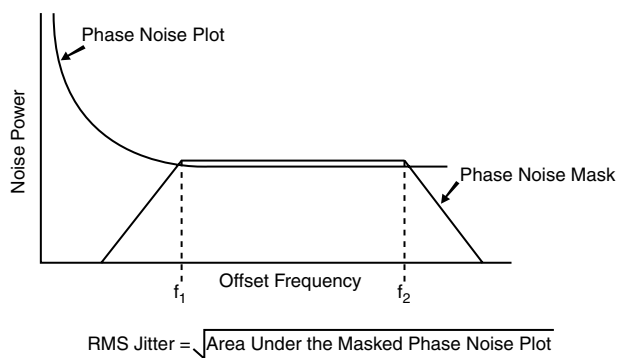
PARAMETER MEASUREMENT INFORMATION



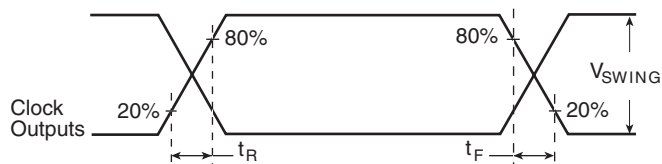
3.3V CORE/3.3V OUTPUT LOAD AC TEST CIRCUIT



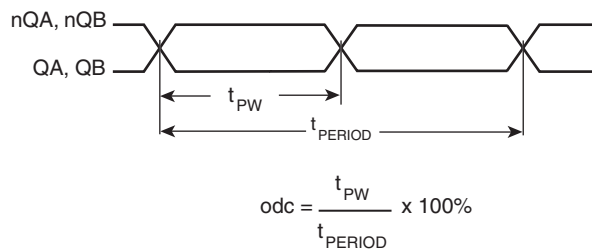
OUTPUT SKEW



RMS PHASE JITTER



OUTPUT RISE/FALL TIME



OUTPUT DUTY CYCLE/PULSE WIDTH/PERIOD

APPLICATION INFORMATION

POWER SUPPLY FILTERING TECHNIQUES

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. The ICS843242 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL. V_{CC} , V_{CCA} , V_{CCO_A} and V_{CCO_B} should be individually connected to the power supply plane through vias, and bypass capacitors should be used for each pin. To achieve optimum jitter performance, power supply isolation is required. *Figure 1* illustrates how a 10Ω resistor along with a $10\mu F$ and a $0.01\mu F$ bypass capacitor should be connected to each V_{CCA} pin.

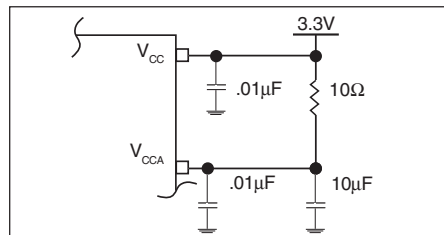


FIGURE 1. POWER SUPPLY FILTERING

CRYSTAL INPUT INTERFACE

The ICS843242 has been characterized with 18pF parallel resonant crystals. The capacitor values shown in *Figure 2* below were determined using a 31.25MHz or 26.041666MHz

18pF parallel resonant crystal and were chosen to minimize the ppm error.

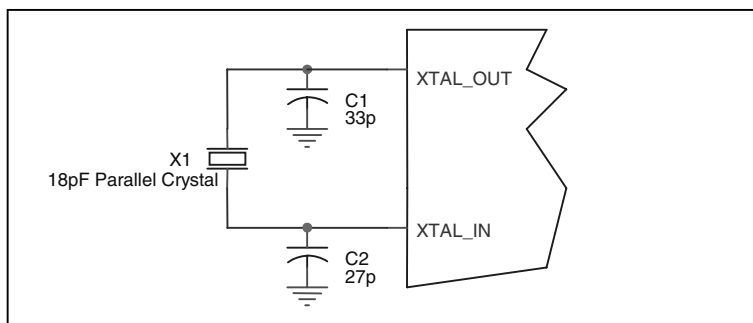


FIGURE 2. CRYSTAL INPUT INTERFACE

LVC MOS TO XTAL INTERFACE

The XTAL_IN input can accept a single-ended LVC MOS signal through an AC coupling capacitor. A general interface diagram is shown in Figure 3. The XTAL_OUT pin can be left floating. The input edge rate can be as slow as 10ns. For LVC MOS inputs, it is recommended that the amplitude be reduced from full swing to half swing in order to prevent signal interference with the power rail and to reduce noise. This configuration requires that the output

impedance of the driver (R_o) plus the series resistance (R_s) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This can be done in one of two ways. First, R_1 and R_2 in parallel should equal the transmission line impedance. For most 50Ω applications, R_1 and R_2 can be 100Ω . This can also be accomplished by removing R_1 and making R_2 50Ω .

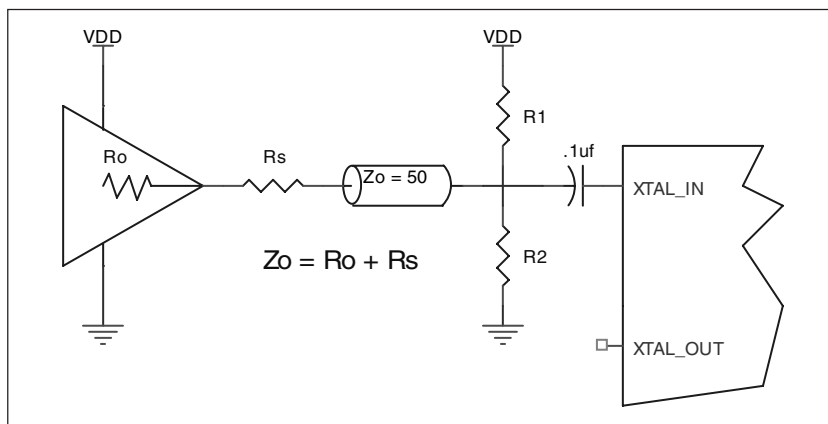


FIGURE 3. GENERAL DIAGRAM FOR LVC MOS DRIVER TO XTAL INPUT INTERFACE

RECOMMENDATIONS FOR UNUSED INPUT AND OUTPUT PINS

INPUTS:

CRYSTAL INPUTS

For applications not requiring the use of the crystal oscillator input, both XTAL_IN and XTAL_OUT can be left floating. Though not required, but for additional protection, a $1k\Omega$ resistor can be tied from XTAL_IN to ground.

LVC MOS CONTROL PINS

All control pins have internal pull-ups or pull-downs; additional resistance is not required but can be added for additional protection. A $1k\Omega$ resistor can be used.

OUTPUTS:

LVPECL OUTPUTS

All unused LVPECL outputs can be left floating. We recommend that there is no trace attached. Both sides of the differential output pair should either be left floating or terminated.

TERMINATION FOR 3.3V LVPECL OUTPUTS

The clock layout topology shown below is a typical termination for LVPECL outputs. The two different layouts mentioned are recommended only as guidelines.

FOUT and nFOUT are low impedance follower outputs that generate ECL/LVPECL compatible outputs. Therefore, terminating resistors (DC current path to ground) or current sources must be used for functionality. These outputs are

designed to drive 50Ω transmission lines. Matched impedance techniques should be used to maximize operating frequency and minimize signal distortion. *Figures 4A and 4B* show two different layouts which are recommended only as guidelines. Other suitable clock layouts may exist and it would be recommended that the board designers simulate to guarantee compatibility across all printed circuit and clock component process variations.

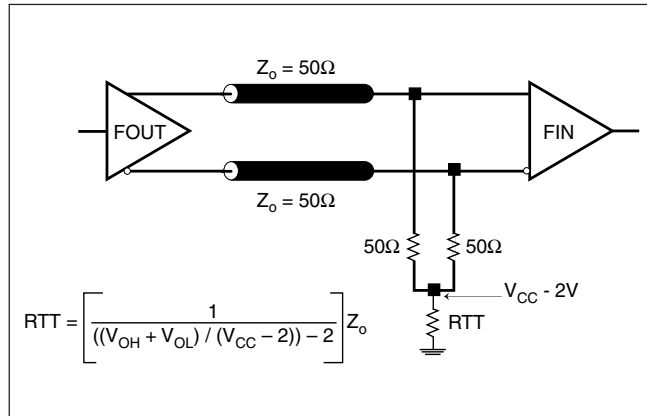


FIGURE 4A. LVPECL OUTPUT TERMINATION

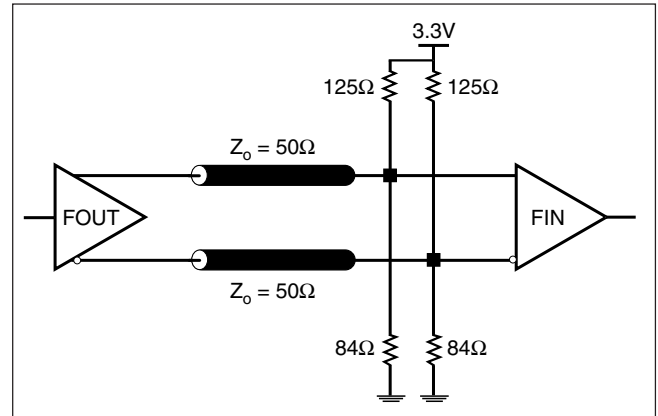


FIGURE 4B. LVPECL OUTPUT TERMINATION

POWER CONSIDERATIONS

This section provides information on power dissipation and junction temperature for the ICS843242. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the ICS843242 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for $V_{CC} = 3.3V + 5\% = 3.465V$, which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)_{MAX} = $V_{CC_MAX} * I_{EE_MAX} = 3.465V * 125mA = 433mW$
- Power (outputs)_{MAX} = **30mW/Loaded Output pair**
If all outputs are loaded, the total power is $2 * 30mW = 60mW$

Total Power_{MAX} (3.465V, with all outputs switching) = $433mW + 60mW = 493mW$

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature for HiPerClockS™ devices is 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 92.4°C/W per Table 7 below.

Therefore, T_j for an ambient temperature of 70°C with all outputs switching is:
 $70°C + 0.493W * 92.4°C/W = 115.5°C$. This is below the limit of 125°C.

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow, and the type of board (single layer or multi-layer).

TABLE 7. THERMAL RESISTANCE θ_{JA} FOR 16-PIN TSSOP, FORCED CONVECTION

θ_{JA} by Velocity (Meters per Second)			
	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	92.4°C/W	88.0°C/W	85.9°C/W

3. Calculations and Equations.

The purpose of this section is to derive the power dissipated into the load.

LVPECL output driver circuit and termination are shown in *Figure 5*.

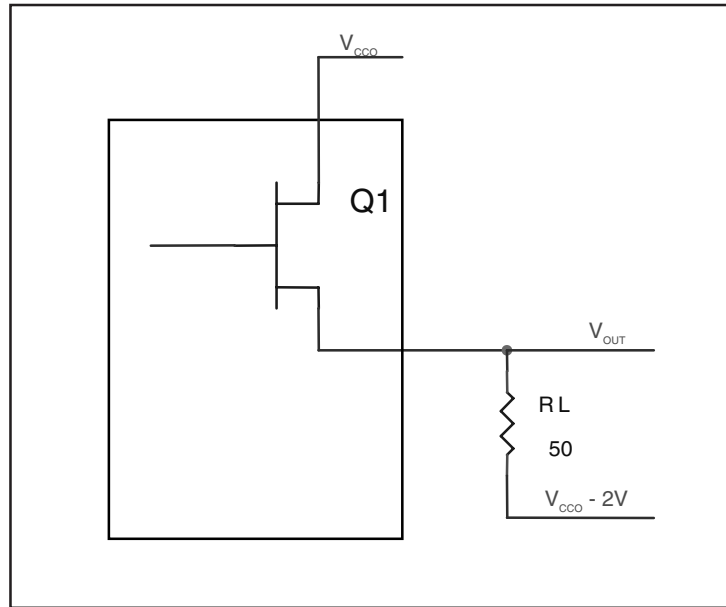


FIGURE 5. LVPECL DRIVER CIRCUIT AND TERMINATION

To calculate worst case power dissipation into the load, use the following equations which assume a 50Ω load, and a termination voltage of $V_{CCO} - 2V$.

- For logic high, $V_{OUT} = V_{OH_MAX} = V_{CCO_MAX} - 0.9V$

$$(V_{CCO_MAX} - V_{OH_MAX}) = 0.9V$$

- For logic low, $V_{OUT} = V_{OL_MAX} = V_{CCO_MAX} - 1.7V$

$$(V_{CCO_MAX} - V_{OL_MAX}) = 1.7V$$

Pd_H is power dissipation when the output drives high.

Pd_L is the power dissipation when the output drives low.

$$Pd_H = [(V_{OH_MAX} - (V_{CCO_MAX} - 2V))/R_L] * (V_{CCO_MAX} - V_{OH_MAX}) = [(2V - (V_{CCO_MAX} - V_{OH_MAX}))/R_L] * (V_{CCO_MAX} - V_{OH_MAX}) = [(2V - 0.9V)/50\Omega] * 0.9V = 19.8mW$$

$$Pd_L = [(V_{OL_MAX} - (V_{CCO_MAX} - 2V))/R_L] * (V_{CCO_MAX} - V_{OL_MAX}) = [(2V - (V_{CCO_MAX} - V_{OL_MAX}))/R_L] * (V_{CCO_MAX} - V_{OL_MAX}) = [(2V - 1.7V)/50\Omega] * 1.7V = 10.2mW$$

$$\text{Total Power Dissipation per output pair} = Pd_H + Pd_L = 30mW$$

RELIABILITY INFORMATION

TABLE 7. θ_{JA} VS. AIR FLOW TABLE FOR 16 LEAD TSSOP

θ_{JA} by Velocity (Meters per Second)			
	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	92.4°C/W	88.0°C/W	85.9°C/W

TRANSISTOR COUNT

The transistor count for ICS843242 is: 3751

PACKAGE OUTLINE - G SUFFIX FOR 16 LEAD TSSOP

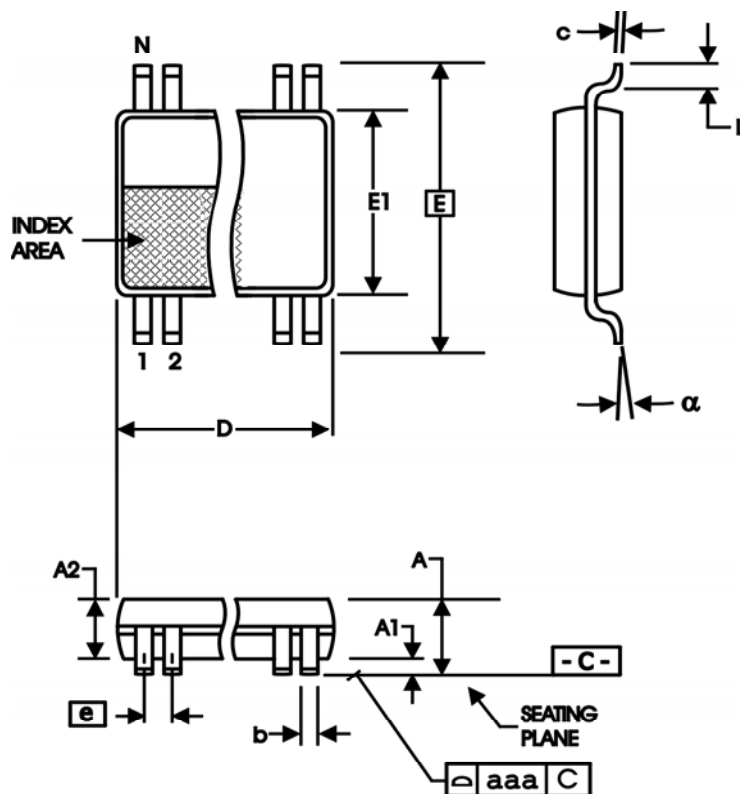


TABLE 8. PACKAGE DIMENSIONS

SYMBOL	Millimeters	
	Minimum	Maximum
N	16	
A	--	1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	4.90	5.10
E	6.40 BASIC	
E1	4.30	4.50
e	0.65 BASIC	
L	0.45	0.75
α	0°	8°
aaa	--	0.10

Reference Document: JEDEC Publication 95, MO-153

TABLE 9. ORDERING INFORMATION

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
ICS843242AG	843242AG	16 Lead TSSOP	tube	0°C to 70°C
ICS843242AGT	843242AG	16 Lead TSSOP	2500 tape & reel	0°C to 70°C
ICS843242AGLF	TBD	16 Lead "Lead-Free" TSSOP	tube	0°C to 70°C
ICS843242AGLFT	TBD	16 Lead "Lead-Free" TSSOP	2500 tape & reel	0°C to 70°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

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